

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): S. Brad Herner et al.	
Application No.: 10/769,047	Group Art Unit: 1762
Filed: 1/30/2004	Examiner: Bret P. Chen
Title: Low Temperature, Low- Resistivity Heavily Doped P-Type Polysilicon Deposition	<b>RECEIVED</b> <b>CENTRAL FAX CENTER</b> <b>MAY 03 2006</b>
Attorney Docket No.: MA-100-I	

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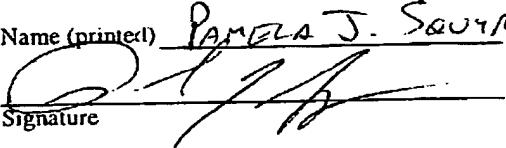
May 3, 2006

**RESPONSE TO NON-FINAL OFFICE ACTION**

This paper is filed in response to the non-final Office Action of February 6, 2006,  
concerning the above-referenced patent application.

A complete list of pending claims begins on page 2. Amendments to the  
specification begin on page 5. A discussion of specification amendments appears on  
page 7. Remarks begin on page 8, and a conclusion appears on page 14.

I hereby certify that this paper is being transmitted by facsimile to the U.S. Patent and Trademark Office on  
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